

L Number	Hits	Search Text	DB	Time stamp
1	1	("5690763").PN.	USPAT	2004/06/12 14:06
2	1	("4467394").PN.	USPAT	2004/06/12 14:14
3	1	("5644395").PN.	USPAT	2004/06/12 14:15
4	97015	doped	USPAT	2004/06/12 14:15
5	67191	intrinsic	USPAT	2004/06/12 14:15
6	333042	silicon	USPAT	2004/06/12 14:15
7	10832	doped adj silicon	USPAT	2004/06/12 14:15
8	741	intrinsic adj silicon	USPAT	2004/06/12 14:15
9	231	(doped adj silicon) and (intrinsic adj silicon)	USPAT	2004/06/12 14:15
10	117928	wafer wafers	USPAT	2004/06/12 14:15
11	116	((doped adj silicon) and (intrinsic adj silicon)) and (wafer wafers )	USPAT	2004/06/12 14:15
12	1069	doped with intrinsic with silicon	USPAT	2004/06/12 14:15
13	29	(doped with intrinsic with silicon) with (wafer wafers )	USPAT	2004/06/12 14:16
14	545321	glass	USPAT	2004/06/12 14:16
16	287903	channels	USPAT	2004/06/12 14:17
17	1	((doped with intrinsic with silicon) with (wafer wafers )) and glass) and channels	USPAT	2004/06/12 14:17
15	10	((doped with intrinsic with silicon) with (wafer wafers )) and glass	USPAT	2004/06/12 14:21
18	0	((("5690763").PN.) and (("4467394").PN.) and (("5644395").PN.)	USPAT	2004/06/12 14:21
20	302219	semiconductor	USPAT	2004/06/12 14:21
21	2	((("5690763").PN.) (("4467394").PN.) ("5644395").PN.) and semiconductor	USPAT	2004/06/12 14:28
22	547424	pyrex glass	USPAT	2004/06/12 14:28
23	533	field adj assisted	USPAT	2004/06/12 14:29
24	44	silicon with (pyrex glass) with (field adj assisted)	USPAT	2004/06/12 14:29
25	3975	oxygen adj ions	USPAT	2004/06/12 14:29
26	0	(silicon with (pyrex glass) with (field adj assisted)) and (oxygen adj ions)	USPAT	2004/06/12 14:29
27	33	(wafer wafers ) and (silicon with (pyrex glass) with (field adj assisted))	USPAT	2004/06/12 14:43
19	3	((("5690763").PN.) (("4467394").PN.) ("5644395").PN.)	USPAT	2004/06/12 14:33
29	0	(field adj assisted) with (oxygen adj ions)	USPAT	2004/06/12 14:43
30	178445	ions	USPAT	2004/06/12 14:43
31	28	(field adj assisted) with ions	USPAT	2004/06/12 14:43
-	333042	silicon	USPAT	2004/06/12 13:26
-	545321	glass	USPAT	2004/06/11 18:12
-	106278	wafer	USPAT	2004/06/11 18:12
-	30371	silicon near wafer	USPAT	2004/06/11 18:13
-	996650	deposit deposited layer layered	USPAT	2004/06/11 18:13
-	668	glass with (silicon near wafer) with (deposit deposited layer layered)	USPAT	2004/06/11 18:20
-	675571	reactor reaction	USPAT	2004/06/11 18:14
-	247	(glass with (silicon near wafer) with (deposit deposited layer layered)) and (reactor reaction)	USPAT	2004/06/11 18:20
-	287903	channels	USPAT	2004/06/11 18:14
-	24	((glass with (silicon near wafer) with (deposit deposited layer layered)) and (reactor reaction)) and channels	USPAT	2004/06/11 18:20
-	21	("4708600"   "4822250"   "4908112"   "5085562"   "5171132"   "5224843"   "5252294"   "5451788"   "5519635"   "5525041"   "5611676"   "5637469"   "5677195"   "5705018"   "5816780"   "5840062"   "5856174"   "5863502"   "5876187"   "5922591"   "6054277").PN.	USPAT	2004/06/11 18:18
-	9522	pyrex	USPAT	2004/06/11 18:20
-	30	pyrex with (silicon near wafer) with (deposit deposited layer layered)	USPAT	2004/06/11 18:20
-	7	(pyrex with (silicon near wafer) with (deposit deposited layer layered)) and (reactor reaction)	USPAT	2004/06/11 18:20

-	6	((pyrex with (silicon near wafer) with (deposit deposited layer layered)) and (reactor reaction)) and channels	USPAT	2004/06/11 18:21
-	94	ashmead.in.	USPAT	2004/06/11 18:21
-	930744	plate	USPAT	2004/06/11 18:21
-	931923	ashmead.in. adn plate	USPAT	2004/06/11 18:21
-	8	ashmead.in. and plate	USPAT	2004/06/11 18:22
-	2	"field assisted bond"	USPAT	2004/06/11 18:28
-	97015	doped	USPAT	2004/06/11 18:31
-	67191	intrinsic	USPAT	2004/06/11 18:31
-	237639	dioxide	USPAT	2004/06/11 18:31
-	476479	aluminum	USPAT	2004/06/11 18:31
-	117654	gold	USPAT	2004/06/11 18:31
-	709708	electric	USPAT	2004/06/11 18:31
-	3	((US-6458325-\$ or US-5644395-\$ or US-4467394-\$).did.	USPAT	2004/06/11 18:32
-	0	doped and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$).did.)	USPAT	2004/06/11 18:32
-	0	intrinsic and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$).did.)	USPAT	2004/06/11 18:32
-	0	dioxide and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$).did.)	USPAT	2004/06/11 18:32
-	0	electric and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$).did.)	USPAT	2004/06/11 18:32
-	1	aluminum and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$).did.)	USPAT	2004/06/11 18:33
-	1	gold and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$).did.)	USPAT	2004/06/11 18:36
-	10832	doped adj silicon	USPAT	2004/06/11 18:36
-	741	intrinsic adj silicon	USPAT	2004/06/11 18:36
-	1052	wafer with (doped adj silicon)	USPAT	2004/06/11 18:36
-	65	wafer with (intrinsic adj silicon)	USPAT	2004/06/11 18:36
-	3	(wafer with (doped adj silicon)) and (wafer with (intrinsic adj silicon))	USPAT	2004/06/11 18:37
-	62822	silicon adj dioxide	USPAT	2004/06/11 18:37
-	4950	wafer with (silicon adj dioxide)	USPAT	2004/06/11 18:37
-	458512	coated	USPAT	2004/06/11 18:37
-	412	(wafer with (silicon adj dioxide)) with coated	USPAT	2004/06/11 18:38
-	225	glass and ((wafer with (silicon adj dioxide)) with coated)	USPAT	2004/06/11 18:38